

ABSTRACT OF THE DISCLOSURE

[0047] A microelectronic component is described having a barrier layer formed from WN_x and a method is described for fabricating such a microelectronic component. The stoichiometry of the barrier formed from WN_x is chosen such that $0.5 > x > 0.3$ holds true. The barrier has a very high thermostability and also a low electrical resistance and is therefore suitable in particular for use in a gate stack.

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